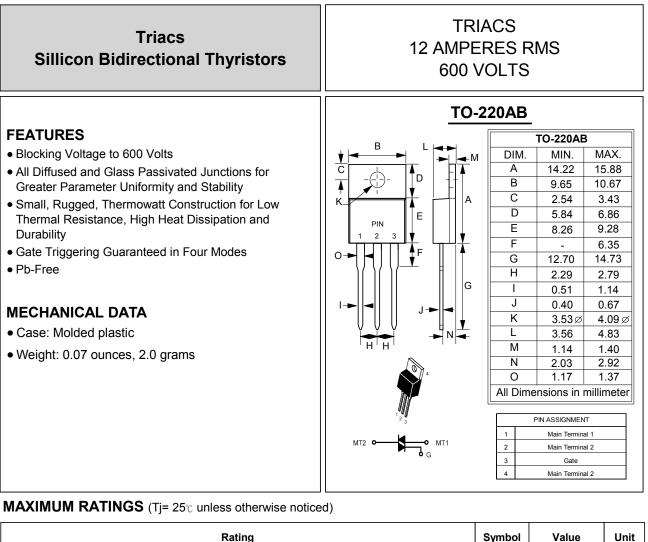
# LITE ON SEMICONDUCTOR

## T12M25F600B



Rating		Value	Unit
Peak Repetitive Off– State Voltage (1) (TJ= -40 to 125 $^\circ$ C, Sine Wave, 50 to 60 Hz; Gate Open)	Vdrm, Vrrm	600	Volts
On-State RMS Current (Tc = +80℃) Full Cycle Sine Wave 50 to 60 Hz	IT(RMS)	12	Amp
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, TJ= +25 $^\circ\!\!\mathbb{C}$ )	Ітѕм	100	Amps
Circuit Fusing Consideration (t = 8.3 ms)	l <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Power (Tc = +80℃, t <= 2 us)	Рдм	16	Watt
Average Gate Power (Tc = +80°C, t =8.3 ms)	PG(AV)	0.35	Watt
Peak Gate Current (Tc = +80°C, t <=2 us)	Igм	4	Amp
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	Tstg	-40 to +150	°C
Notice: (1) VDRM and VRRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the	RE	V. 3, Oct-2010, K	TXC30

# THERMAL CHARACTERISTICS Characteristic Symbol Value Unit Thermal Resistance - Junction to Case Rth.JC 2.2 °C/W Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds TL 260 °C

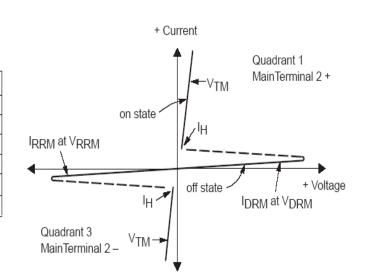
#### ELECTRICAL CHARACTERISTICS (TJ=25°C unless otherwise noted, Electrical apply in both directions)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1			1	
Peak Reptitive Forward or Reverse Blocking CurrentTJ=25°C(VD=Rated VDRM, VRRM; Gate Open)TJ=100°C	IDRM IRRM			10 2.0	uA mA
ON CHARACTERISTICS					
Peak On-State Voltage (ITM=± 17A Peak @Tp $\leq$ 2.0 ms, Duty Cycle $\leq$ 2%)	VTM		1.7	2.0	Volts
Gate Trigger Current (VD = 12Vdc; RL = 100 Ohms)	IGT1 IGT2 IGT3 IGT4		10 20 15 30	25 60 25 60	mA
Gate Trigger Voltage (V <sub>D</sub> = 12 Vdc; R <sub>L</sub> =100 Ohms)	VGT1 VGT2 VGT3 VGT4	  	1.25 1.25 1.25 1.25 1.25	2.5 2.5 2.5 2.5	Volts
Holding Current (VD = 12 V, Initiating Current = ± 200 mA, Gate Open)	Ін		15	30	mA
Gate Non - Trigger Voltage (VD =12 V, RL =100 Ohms, TC=100℃)	Vgd	0.2			Volts
Gate-Controlled Turn-On Time (VD = Rated VDRM , ITM = 10 A, IGT =80 mA, Rise Time=0.1 us)	tgt		1.6		us

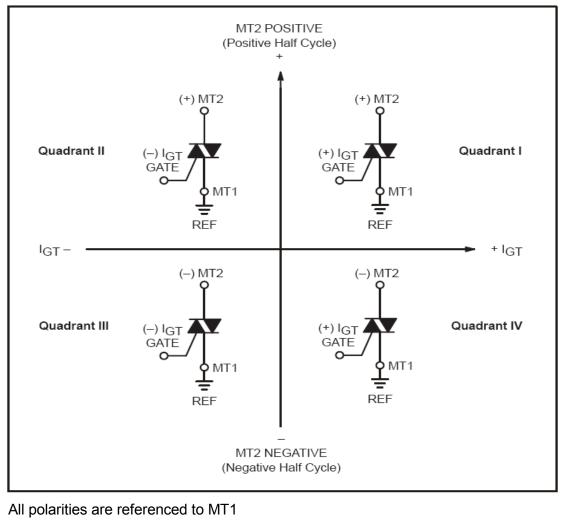
#### **DYNAMIC CHARACTERISTICS**

Critical Rate of Rise of Off-State Voltage (VD=Rated VDRM, Exponential Voltage Rise, Gate Open Tc=100°C)	dv/dt	60		 V/us
Critical Rate of Rise of Commutation Voltage (VD = Rated VDRM , $I_{TM}$ = 8 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, TC = 80°C)	dv/dt(c)		10	 V/us

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
VTM	Maximum On State Voltage
ΙΗ	Holding Current



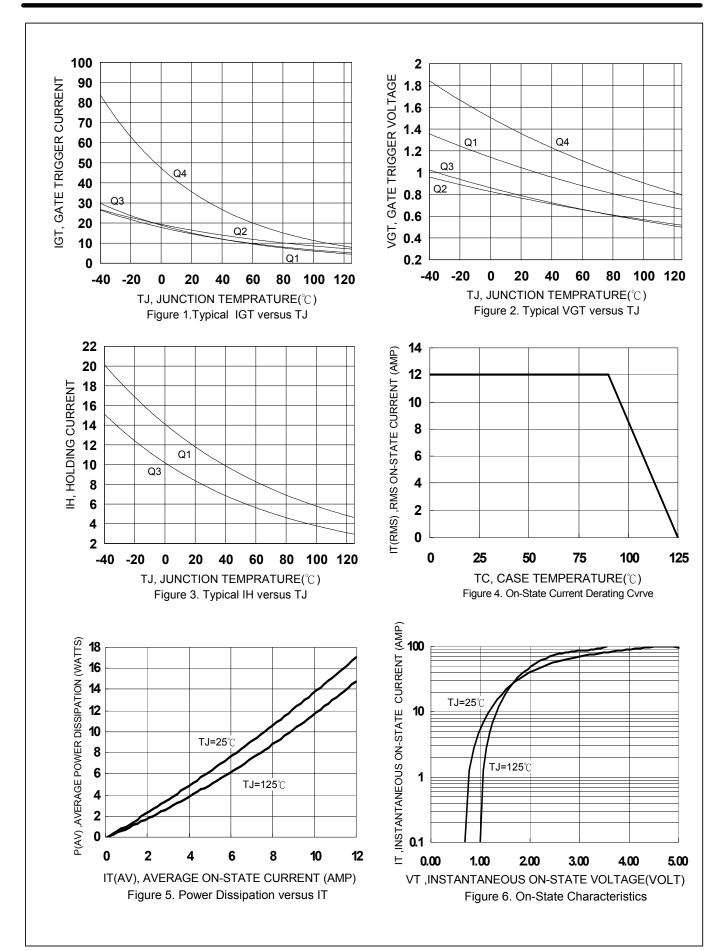
## **Quadrant Definitions**



Whith in -phase signal (using standard AC lines) quadrants I and III are used

# **LITE ON**

#### RATING AND CHARACTERISTIC CURVES T12M25F600B



## LITE ON



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